COMPLIANT

HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt®



| PRIMARY CHARACTERISTICS | | | | |
|----------------------------------|-------------|--|--|--|
| I _{F(AV)} | 15 A | | | |
| V _R | 600 V | | | |
| V _F at I _F | 1.25 V | | | |
| t _{rr} (typ.) | 21 ns | | | |
| T _J max. | 175 °C | | | |
| Package | TO-220AC 2L | | | |
| Circuit configuration | Single | | | |

FEATURES

- · Hyperfast soft recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Peak repetitive reverse voltage | V_{RRM} | | 600 | V |
| Average rectified forward current in DC | I _{F(AV)} | T _C = 149 °C | 15 | ۸ |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 160 | Α |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to +175 | °C |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|-------------------------------------|--|-----|------|-------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS MIN. TYP. MA | | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 600 | - | - | |
| Forward voltage | V | I _F = 15 A | - | 1.8 | 2.45 | V |
| Forward voltage | V _F | I _F = 15 A, T _J = 150 °C | - | 1.25 | 1.6 | |
| Develope legicome eviment | | V _R = V _R rated | - | 0.01 | 15 | |
| Reverse leakage current | I _R | T _J = 150 °C, V _R = V _R rated | - | 20 | 200 | μA |
| Junction capacitance | Ст | V _R = 600 V | = | 12 | - | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8 | - | nH |



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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---|--|--|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | $I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 21 | 26 | | |
| Davaga gaaayan tima | | I _F = 15 A, dI _F /dt = 100 | $I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | 25 | 36 | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 29 | - | ns |
| | | T _J = 125 °C | $I_F = 15 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 390 \text{ V}$ | - | 65 | 65 - | |
| Dealeman | irrent I _{RRM} | T _J = 25 °C | | - | 3.9 | - | A |
| Peak recovery current | | T _J = 125 °C | | - | 7.0 | - | |
| Doverno vocaveni oberno | 0 | T _J = 25 °C | | - | 60 | - | nC |
| Reverse recovery charge | Q _{rr} | T _J = 125 °C | | - | 240 | - | nc |
| Reverse recovery time | t _{rr} | T _J = 125 °C | I _F = 15 A, dI _F /dt = 800 A/μs, V _R = 390 V | - | 42 | - | ns |
| Peak recovery current | I _{RRM} | | | - | 21 | - | Α |
| Reverse recovery charge | Q _{rr} | | | - | 480 | - | nC |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|--|----------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C |
| Thermal resistance, junction-to-case | R _{thJC} | | - | 1.2 | 1.4 | |
| Thermal resistance, junction-to-ambient | R _{thJA} | Typical socket mount | - | - | 70 | °C/W |
| Typical thermal resistance, case-to-heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | |
| Weight | | | - | 2 | - | g |
| Weight | | | - | 0.07 | - | oz. |
| Mounting torque | | | 6 (5) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style TO-220AC 2L | | ETH | 1506 | |



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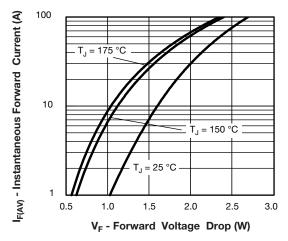


Fig. 1 - Typical Forward Voltage Drop Characteristics

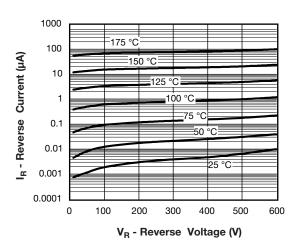


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

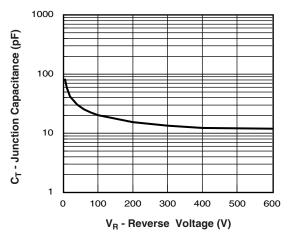


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

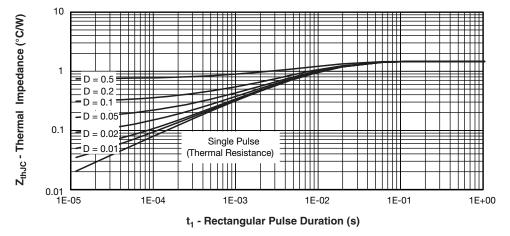


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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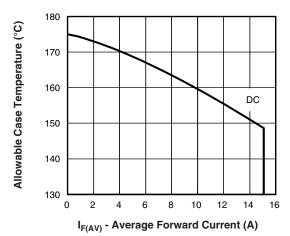


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

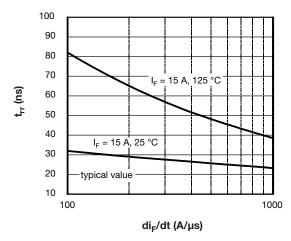


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

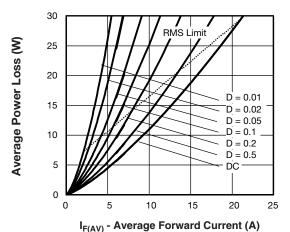


Fig. 6 - Forward Power Loss Characteristics

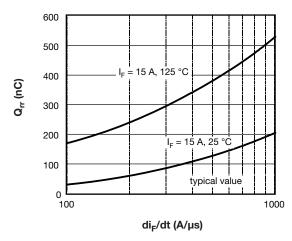
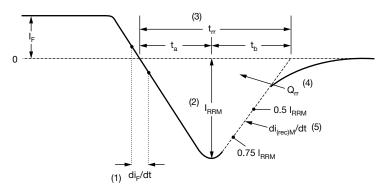


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) \mathbf{I}_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{F}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

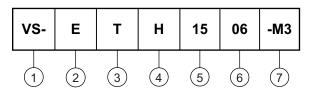
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = 2L TO-220AC

4 - H = hyperfast recovery time

5 - Current code: 15 = 15 A

Voltage code: 06 = 600 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | |
|--------------------------------|---------------|--------------------------|--|--|
| PREFERRED P/N | BASE QUANTITY | PACKAGING DESCRIPTION | | |
| VS-ETH1506-M3 | 50 | Antistatic plastic tubes | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|--|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?96156</u> | | | | |
| Part marking information | www.vishay.com/doc?95391 | | | |



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